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DRV8313 TRIPLE HALF-H-BRIDGE DRIVER IC

Check for Samples: DRV8313

FEATURES

- Three Half-H-Bridge Driver IC
 - Drives 3-Phase Brushless DC Motors
 - Individual Half-Bridge Control
 - Pins for Low-Side Current Sensing
 - Low MOSFET On-Resistance
- 2.5-A Maximum Drive Current at 24 V, 25°C
- **Uncommitted Comparator Can Be Used for Current Limit or Other Functions**
- Built-In 3.3-V 10-mA LDO Regulator
- 8-V to 60-V Operating Supply Voltage Range
- **Thermally Enhanced Surface-Mount Package**

APPLICATIONS

- **HVAC Motors**
- **Consumer Products**
- **Office Automation Machines**
- **Factory Automation**
- **Robotics**

DESCRIPTION

The DRV8313 provides three individually controllable half-H-bridge drivers. It is intended to drive a threephase brushless dc motor, though it can also be used to drive solenoids or other loads. Each output driver channel consists of N-channel power MOSFETs configured in a half-H-bridge configuration. The design brings the ground terminals of each driver to pins, to allow one to perform current sensing on each output.

Current-limit circuitry or other functions are possible uses of an uncommitted comparator.

The DRV8313 can supply up to 2.5-A peak or 1.75-A rms output current per channel (with proper PCB heatsinking at 24 V and 25°C) per half-H-bridge.

The device provides internal shutdown functions for overcurrent protection, short-circuit protection, undervoltage lockout, and overtemperature.

The DRV8313 comes in a 28-pin HTSSOP PowerPAD[™] package.

ORDERING INFORMATION⁽¹⁾

ORDERABLE PART NUMBER	PACKAGE ⁽²⁾	TOPSIDE MARKING	SHIPPING
DRV8313PWPR			Reel of 2000
DRV8313PWP	HTSSOP – PWP	DRV8313	Tube of 50

For the most-current packaging and ordering information, see the Package Option Addendum at the end of this document, or see the TI (1)Web site at www.ti.com.

See package drawings, thermal data, and symbolization at www.ti.com/packaging. (2)



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DRV8313



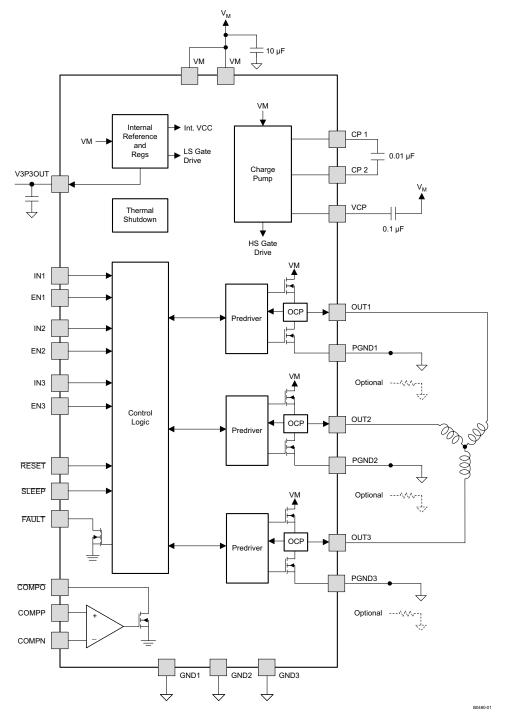
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This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

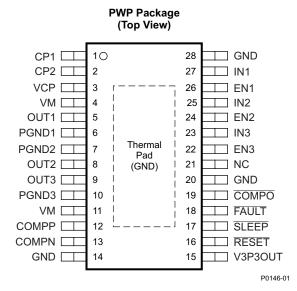
ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

FUNCTIONAL BLOCK DIAGRAM





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PIN DESCRIPTIONS

F	PIN	-	DECODIDEION	
NAME	NO.	TYPE	DESCRIPTION	EXTERNAL COMPONENTS OR CONNECTIONS
Power and	I Ground			
CP1	1	Ю	Charge-pump flying capacitor	
CP2	2	Ю	Charge-pump flying capacitor	Connect a 0.01-µF 100-V capacitor between CP1 and CP2.
GND	12, 20, 28, PPAD	_	Device ground	Connect to system ground
V3P3OUT	15	0	3.3-V regulator output	Bypass to GND with a 0.47-µF 6.3-V ceramic capacitor. Use for suppling external loads is permissible.
VCP	3	Ю	High-side gate drive voltage	Connect a 0.1-µF 16-V ceramic capacitor to VM.
VM	4, 11	-	Main power supply	Connect to power supply (8.2 V–60 V). Connect both pins to the same supply. Bypass to GND with a $10-\mu F$ (minimum) capacitor.
Control				
EN1	26	Ι	Channel 1 enable	Logic high enables OUT1. Internal pulldown
EN2	24	Ι	Channel 2 enable	Logic high enables OUT2. Internal pulldown
EN3	22	I	Channel 3 enable	Logic high enables OUT3. Internal pulldown
IN1	27	Ι	Channel 1 input	Logic input controls state of OUT1. Internal pulldown
IN2	25	l	Channel 2 input	Logic input controls state of OUT2. Internal pulldown
IN3	23	Ι	Channel 3 input	Logic input controls state of OUT3. Internal pulldown
nRESET	16	I	Reset input	Active-low reset input initializes internal logic and disables the outputs. Internal pulldown
nSLEEP	17	I	Sleep-mode input	Logic high to enable device, logic low to enter low-power sleep mode. Internal pulldown
Status			·	
nFAULT	18	OD	Fault	Logic low when in fault condition (overtemperature, overcurrent, UVLO)
Comparate	or			
COMPN	13	I	Comparator negative input	Negative input of comparator
COMPP	12	Ι	Comparator positive input	Positive input of comparator
nCOMPO	19	OD	Comparator out	Output of comparator. Open-drain output

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PIN DESCRIPTIONS (continued)

PI	N	ТҮРЕ	DESCRIPTION	
NAME	NO.	ITPE	DESCRIPTION	EXTERNAL COMPONENTS OR CONNECTIONS
Output				
OUT1	5	0	Output 1	
OUT2	8	0	Output 2	Connect to loads.
OUT3	9	0	Output 3	
PGND1	6	-	Ground for OUT1	
PGND2	7	-	Ground for OUT2	Connect to ground, or to low-side current-sense resistors.
PGND3	10	-	Ground for OUT3	

ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range (unless otherwise noted)⁽¹⁾⁽²⁾

		VALUE	UNIT
	Power-supply voltage range (V _M)	–0.3 V to 65	V
	Digital-pin voltage range	-0.5 to 7	V
	Comparator input-voltage range	-0.5 to 7	V
	Peak motor-drive output current	Internally limited	A
	Pin voltage (GND1, GND2, GND3)	±600	mV
	Continuous motor-drive output current ⁽³⁾	2.5	А
TJ	Operating virtual junction temperature range	-40 to 150	°C
T _{stg}	Storage temperature range	-60 to 150	°C

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltage values are with respect to the network ground terminal.

(3) Observe power dissipation and thermal limits.

THERMAL INFORMATION

		DRV8313	
	THERMAL METRIC ⁽¹⁾	PWP	UNIT
		28 PINS	
θ _{JA}	Junction-to-ambient thermal resistance ⁽²⁾	31.6	°C/W
θ _{JCtop}	Junction-to-case (top) thermal resistance ⁽³⁾	15.9	°C/W
θ _{JB}	Junction-to-board thermal resistance ⁽⁴⁾	5.6	°C/W
Ψ _{JT}	Junction-to-top characterization parameter ⁽⁵⁾	0.2	°C/W
Ψ _{JB}	Junction-to-board characterization parameter ⁽⁶⁾	5.5	°C/W
θ _{JCbot}	Junction-to-case (bottom) thermal resistance ⁽⁷⁾	1.4	°C/W

For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, SPRA953.
 The junction-to-ambient thermal resistance under natural convection is obtained in a simulation on a JEDEC-standard, high-K board, as

specified in JESD51-7, in an environment described in JESD51-2a.

(3) The junction-to-case (top) thermal resistance is obtained by simulating a cold plate test on the package top. No specific JEDECstandard test exists, but a close description can be found in the ANSI SEMI standard G30-88.

(4) The junction-to-board thermal resistance is obtained by simulating in an environment with a ring cold plate fixture to control the PCB temperature, as described in JESD51-8.

(5) The junction-to-top characterization parameter, ψ_{JT} , estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining θ_{JA} , using a procedure described in JESD51-2a (sections 6 and 7).

(6) The junction-to-board characterization parameter, ψ_{JB} , estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining θ_{JA} , using a procedure described in JESD51-2a (sections 6 and 7).

(7) The junction-to-case (bottom) thermal resistance is obtained by simulating a cold plate test on the exposed (power) pad. No specific JEDEC standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.



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RECOMMENDED OPERATING CONDITIONS

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V _M	Motor power-supply voltage range ⁽¹⁾	8		60	V
V _{GNDX}	GND1, GND2, GND3 pin voltage	-500	0	500	mV
I _{V3P3}	V3P3OUT load current	0		10	mA

(1) All $V_{\rm M}$ pins must be connected to the same supply voltage.

ELECTRICAL CHARACTERISTICS

 $T_A = 25^{\circ}C$, over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Power S	upplies					
I _{VM}	VM operating supply current	V _M = 24 V, f _{PWM} < 50 kHz		1	5	mA
I _{VMQ}	VM sleep-mode supply current	V _M = 24 V		500	800	μA
V _{UVLO}	VM undervoltage lockout voltage	V _M rising		6.3	8	V
V3P3OU	T Regulator	· · ·				
V _{3P3}	V3P3OUT voltage	I _{OUT} = 0 to 10 mA	3.1	3.3	3.52	V
Logic-Le	evel Inputs	· · · ·			I	
V _{IL}	Input low voltage			0.6	0.7	V
VIH	Input high voltage		2.2		5.25	V
V _{HYS}	Input hysteresis		50		600	mV
I _{IL}	Input low current	VIN = 0	-5		5	μA
IIH	Input high current	VIN = 3.3 V			100	μA
R _{PD}	Pulldown resistance			100		kΩ
nFAULT	and COMPO OutputS (Open-Drain Out	puts)			I	
V _{OL}	Output low voltage	I _O = 5 mA			0.5	V
l _{он}	Output high leakage current	V _O = 3.3 V			1	μA
Compara	ator	· · · ·			I	
V _{CM}	Common-mode input-voltage range		0		5	V
V _{IO}	Input offset voltage		-7		7	mV
I _{IB}	Input bias current		-300		300	nA
t _R	Response time	100-mV step with 10-mV overdrive			2	μs
H-Bridge	FETs					
		$V_{\rm M} = 24 \text{ V}, \text{ I}_{\rm O} = 1 \text{ A}, \text{ T}_{\rm J} = 25^{\circ}\text{C}$		0.24		-
r _{ds(on)}	High-side FET on-resistance	V _M = 24 V, I _O = 1 A, T _J = 85°C		0.29	0.39	Ω
		$V_{\rm M} = 24 \text{ V}, \text{ I}_{\rm O} = 1 \text{ A}, \text{ T}_{\rm J} = 25^{\circ}\text{C}$		0.24		0
r _{ds(on)}	Low-side FET on-resistance	$V_{\rm M} = 24 \text{ V}, \text{ I}_{\rm O} = 1 \text{ A}, \text{ T}_{\rm J} = 85^{\circ}\text{C}$		0.29	0.39	Ω
I _{OFF}	Off-state leakage current		-2		2	μA
t _{DEAD}	Output dead time			90		ns
	on Circuits	·			1	
IOCP	Overcurrent protection trip level		3			А
t _{OCP}	Overcurrent protection deglitch time			5		μs
T _{TSD}	Thermal shutdown temperature	Die temperature	150	160	180	°C

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STRUMENTS

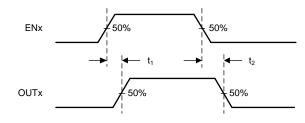
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SWITCHING CHARACTERISTICS⁽¹⁾

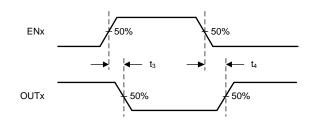
$T_A = 25^\circ$, $V_M = 24$ V, $R_L = 20 \Omega$

NO.	PARAMETER	DESCRIPTION	MIN	MAX	UNIT
1	t ₁	Delay time, ENx high to OUTx high, INx = 1	130	330	ns
2	t ₂	Delay time, ENx low to OUTx low, INx = 1	275	475	ns
3	t ₃	Delay time, ENx high to OUTx low, INx = 0	100	300	ns
4	t ₄	Delay time, ENx low to OUTx high, INx = 0	200	400	ns
5	t ₅	Delay time, INx high to OUTx high	300	500	ns
6	t ₆	Delay time, INx low to OUTx low	275	475	ns
7	tr	Output rise time, resistive load to GND	30	150	ns
8	t _f	Output fall time, resistive load to GND	30	150	ns

(1) Not production tested



INx = 1, Resistive Load to GND



80%

20%

tr

OUTx

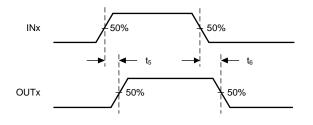


80%

20%

t.

T0543-01



ENx = 1, Resistive Load to GND

Figure 1. DRV8313 Switching Characteristics



FUNCTIONAL DESCRIPTION

Output Stage

The DRV8313 contains three half-H-bridge drivers. The source terminals of the low-side FETs of all three half-Hbridges terminate at separate pins (GND1, GND2, and GND3) to allow the use of a low-side current-sense resistor on each output, if desired. The user may also connect all three together to a single low-side sense resistor, or may connect them directly to ground if there is no need for current sensing.

If using a low-side sense resistor, take care to ensure that the voltage on the GND1, GND2, or GND3 pin does not exceed ±500 mV.

Note that there are multiple VM motor power-supply pins. Connect all VM pins together to the motor-supply voltage.

Bridge Control

The INx input pins directly control the state (high or low) of the OUTx outputs; the ENx input pins enable or disable the OUTx driver. The following table shows the logic:

INx	ENx	OUTx
Х	0	Z
0	1	L
1	1	Н

Charge Pump

Because the output stages use N-channel FETs, the device requires a gate-drive voltage higher than the VM power supply to enhance the high-side FETs fully. The DRV8313 integrates a charge-pump circuit that generates a voltage above the VM supply for this purpose.

The charge pump requires two external capacitors for operation. See the block diagram and pin descriptions for details on these capacitors (value, connection, and so forth).

The charge pump shuts down when nSLEEP is active-low.

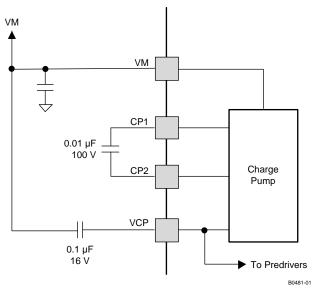


Figure 2. DRV8313 Charge Pump



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Comparator

The DRV8313 includes an uncommitted comparator, which can find use as a current-limit comparator or for other purposes.

The following diagram shows connections to use the comparator to sense current for implementing a current limit. Current from all three low-side FETs is sensed using a single low-side sense resistor. The voltage across the sense resistor is compared with a reference, and when the sensed voltage exceeds the reference, a current-limit condition is signaled to the controller. The V3P3OUT internal voltage regulator can be used to set the reference voltage of the comparator.

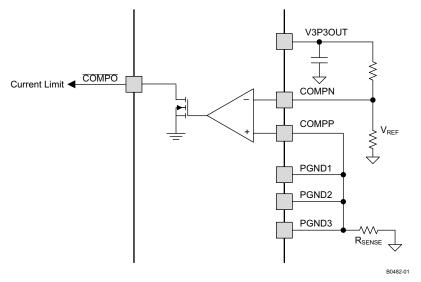


Figure 3. DRV8313 Comparator

nRESET and nSLEEP Operation

The nRESET pin, when driven active-low, resets any faults. It also disables the output drivers while it is active. The device ignores all inputs while nRESET is active. Note that there is an internal power-up-reset circuit, so that driving nRESET at power up is not required.

Driving nSLEEP low puts the device into a low-power sleep state. Entering this state disables the output drivers, stops the gate-drive charge pump, resets all internal logic (including faults), and stops all internal clocks. In this state, the device ignores all inputs until nSLEEP returns inactive-high. When returning from sleep mode, some time (approximately 1 ms) must pass before the motor driver becomes fully operational. Note that the V3P3 regulator remains operational in sleep mode.

Protection Circuits

The DRV8313 has full protection against undervoltage, overcurrent, and overtemperature events.

OVERCURRENT PROTECTION (OCP)

An analog current-limit circuit on each FET limits the current through the FET by removing the gate drive. If this analog current limit persists for longer than the OCP deglitch time, the device disables the channel experiencing the overcurrent and drives the nFAULT pin low. The driver remains off until either assertion of nRESET or the cycling of VM power.

Overcurrent conditions on both high- and low-side devices, that is, a short to ground, supply, or across the motor winding, all result in an overcurrent shutdown.

THERMAL SHUTDOWN (TSD)

If the die temperature exceeds safe limits, the device disables all outputs and drives the nFAULT pin low. Once the die temperature has fallen to a safe level, operation automatically resumes.



UNDERVOLTAGE LOCKOUT (UVLO)

If at any time the voltage on the VM pins falls below the undervoltage-lockout threshold voltage, the device disables all outputs, resets internal logic, and drives the nFAULT pin low. Operation resumes when VM rises above the UVLO threshold.

THERMAL INFORMATION

Thermal Protection

The DRV8313 has thermal shutdown (TSD) as previously described. A die temperature in excess of approximately 150°C disables the device until the temperature drops to a safe level.

Any tendency of the device to enter thermal shutdown is an indication of excessive power dissipation, insufficient heatsinking, or too high an ambient temperature.

Power Dissipation

The power dissipated in the output FET resistance, or r_{DS(on)} dominates power dissipation in the DRV8313. A rough estimate of average power dissipation of each half-H-bridge when running a static load is:

 $P = r_{DS(on)} \times (I_{OUT})^2$

(1)

where P is the power dissipation of one H-bridge, $r_{DS(on)}$ is the resistance of each FET, and I_{OUT} is equal to the average current drawn by the load. Note that at start-up and fault conditions, this current is much higher than normal running current; remember to take these peak currents and their duration into consideration.

The total device dissipation is the power dissipated in each of the three half-H-bridges added together.

The maximum amount of power that the device can dissipate depends on ambient temperature and heatsinking.

Note that $r_{DS(on)}$ increases with temperature, so as the device heats, the power dissipation increases. Take this into consideration when sizing the heatsink.

Heatsinking

The PowerPAD package uses an exposed pad to remove heat from the device. For proper operation, this pad must be thermally connected to copper on the PCB to dissipate heat. On a multi-layer PCB with a ground plane, add a number of vias to connect the thermal pad to the ground plane to accomplish this. On PCBs without internal planes, add copper area on either side of the PCB to dissipate heat. If the copper area is on the opposite side of the PCB from the device, use thermal vias to transfer the heat between the top and bottom layers.

For details about how to design the PCB, see TI Application Report SLMA002, *PowerPAD Thermally Enhanced Package* and TI Application Brief SLMA004, *PowerPAD Made Easy*, available at www.ti.com.

In general, providing more copper area allows the dissipation of more power.

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APPLICATION INFORMATION

Output Configurations and Connections

The typical application for the DRV8313 is to drive a 3-phase brushless motor. In this application, the three outputs connect to the three motor leads, as shown in Figure 4.

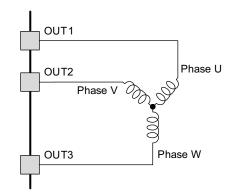


Figure 4. Three-Phase Motor Connection

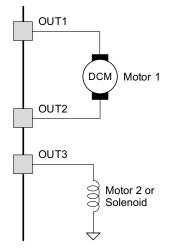
The device achieves standard 120° (also called trapezoidal or block) commutation, using synchronous rectification, by following the states shown in Table 1

Ctata	OUT1 (Phase U)			OUT2 (Phase V)			OUT3 (Phase W)		
State	IN1	EN1	OUT1	IN2	EN2	OUT2	IN3	EN3	OUT3
1	Х	0	Z	1 / PWM	1	H / PWM	0	1	L
2	1 / PWM	1	H / PWM	Х	0	Z	0	1	L
3	1 / PWM	1	H / PWM	0	1	L	Х	0	Z
4	х	0	Z	0	1	L	1 / PWM	1	H / PWM
5	0	1	L	Х	0	Z	1 / PWM	1	H / PWM
6	0	1	L	1 / PWM	1	H / PWM	Х	0	Z

Table 1. Three-Phase Motor Signals

On can implement asynchronous rectification by also applying the PWM signal to the enable inputs.

The DRV8313 can drive other loads, including dc brush motors and solenoids. For example, one could drive a dc brush motor in both directions, plus a single solenoid or unidirectional dc brush motor:







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The functions would be as shown in Table 2.

								•		
		Motor 2 or Solenoid								
Function	IN1	EN1	OUT1	IN2	EN2	OUT2	Function	IN3	EN3	OUT3
Off or coast	Х	0	Z	Х	х	х	On	1 / PWM	1	1
Off or coast	Х	х	Х	х	0	х	Off or slow decay	0	1	0
Forward	1 / PWM	1	1	0	1	0	Off or coast	х	0	х
Reverse	0	1	0	1 / PWM	1	1				
Brake or slow decay	0	1	0	0	1	0				
Brake or slow decay	1	1	1	1	1	1				

 Table 2. Bidirectional Motor Plus Motor or Solenoid Signals

Applying a PWM signal to the appropriate INx pin(s) as shown in Table 2 could implement PWM speed control.

Another possibility is controlling three different loads. Note that it is possible to return one side of the load either to the power supply (VM) or to ground.

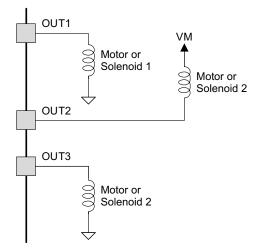


Figure 6. Three Independent Load Connections

	lab	le 3. Three Independent Load Signa	ais
4		Motor or Solonoid 2	Мо

Motor or Solenoid 1				Motor or Solenoid 2				Motor or Solenoid 3			
Function	IN1	EN1	OUT1	Function	IN2	EN2	OUT2	Function	IN3	EN3	OUT3
On	1 / PWM	1	1	On	1 / PWM	1	1	On	1 / PWM	1	1
Off or slow decay	0	1	0	Off or slow decay	0	1	0	Off or slow decay	0	1	0
Off or coast	х	0	х	Off or coast	х	0	х	Off or coast	х	0	Х



24-Jan-2013

PACKAGING INFORMATION

Orderable Device	Status	Package Type	•	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Top-Side Markings	Samples
	(1)		Drawing			(2)		(3)		(4)	
DRV8313PWP	ACTIVE	HTSSOP	PWP	28	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	-40 to 85	DRV8313	Samples
DRV8313PWPR	ACTIVE	HTSSOP	PWP	28	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	-40 to 85	DRV8313	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between

the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ Only one of markings shown within the brackets will appear on the physical device.

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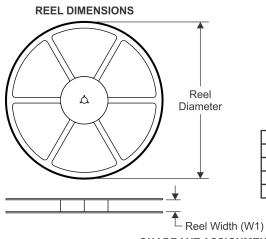
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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

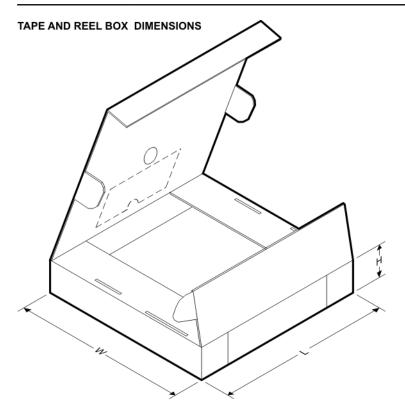
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
DRV8313PWPR	HTSSOP	PWP	28	2000	330.0	16.4	6.9	10.2	1.8	12.0	16.0	Q1

TEXAS INSTRUMENTS

www.ti.com

PACKAGE MATERIALS INFORMATION

26-Jan-2013

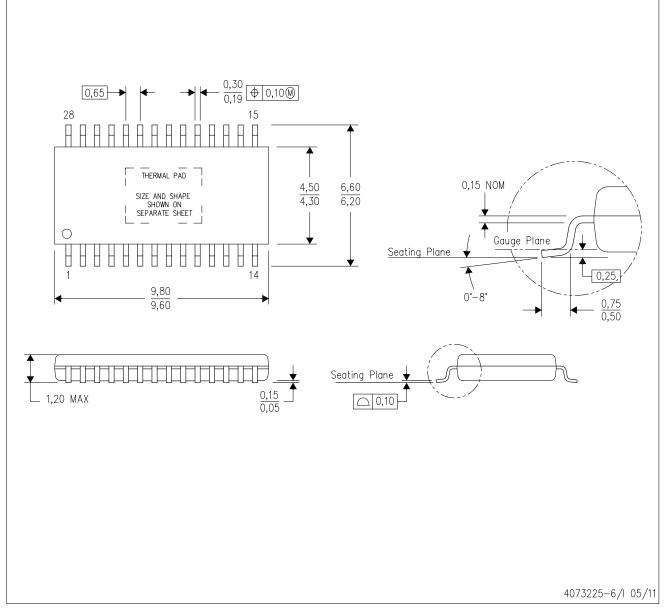


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
DRV8313PWPR	HTSSOP	PWP	28	2000	367.0	367.0	38.0

PWP (R-PDSO-G28)

PowerPAD[™] PLASTIC SMALL OUTLINE

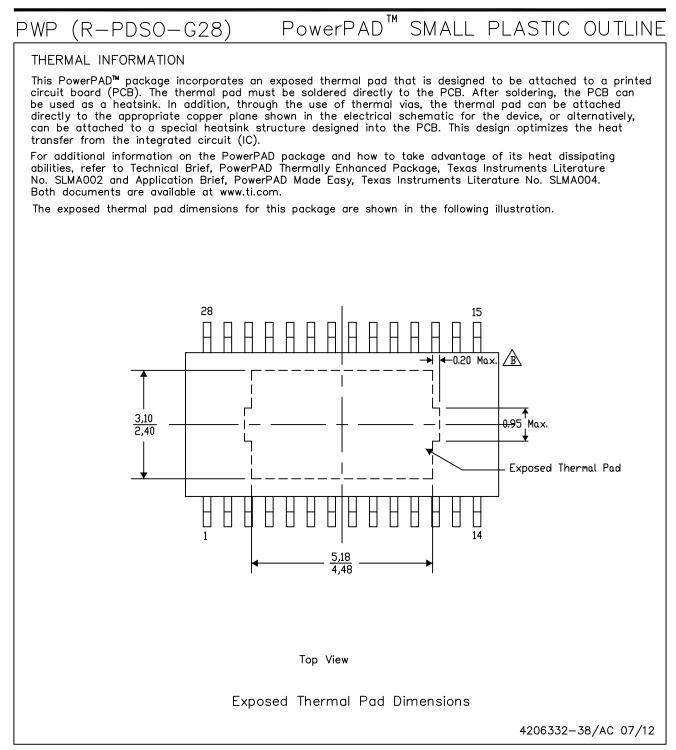


All linear dimensions are in millimeters. NOTES: Α.

- Β. This drawing is subject to change without notice.
- Body dimensions do not include mold flash or protrusions. Mold flash and protrusion shall not exceed 0.15 per side. C.
- This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad D.
- Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 for information regarding recommended board layout. This document is available at www.ti.com http://www.ti.com. E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions. E. Falls within JEDEC MO-153

PowerPAD is a trademark of Texas Instruments.

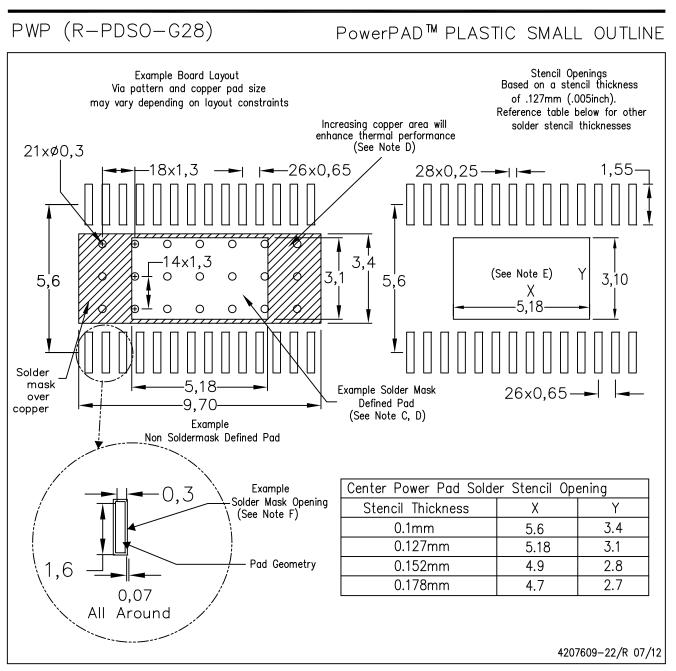




NOTE: A. All linear dimensions are in millimeters <u>A</u> Exposed tie strap features may not be present.

PowerPAD is a trademark of Texas Instruments





NOTES:

A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002, SLMA004, and also the Product Data Sheets.
- E. For specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <htp://www.ti.com>. Publication IPC-7351 is recommended for alternate designs. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil
- F. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



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